

μ PA2630T1R

P-CHANNEL MOSFET $-12 \text{ V}, -7.0 \text{ A}, 28 \text{ m}\Omega$

R07DS0990EJ0100 Rev.1.00 Dec 27, 2012

Description

The μ PA2630T1R is P-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- -1.8V drive available
- Low on-state resistance
 - --- R_{DS (on)1} = 28 mΩ MAX. (V_{GS} = -4.5 V, I_D = -3.5 A)
 - --- $R_{DS (on)2}$ = 35 mΩ MAX. (V_{GS} = -2.5 V, I_D = -3.5 A)
 - --- R_{DS (on)2} = 59 mΩ MAX. (V_{GS} = -1.8 V, I_D = -3.5 A)
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020

Ordering Information

Part Number	Package	
μPA2630T1R-E2-AX*1	6pinHUSON2020	

Note: *1.Pb-free (This product does not contain Pb in the external electrode and other parts.)

Absolute Maximum Ratings (T_A = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V_{DSS}	-12	V
Gate to Source Voltage (V _{DS} = 0 V)	V_{GSS}	∓8	V
Drain Current (DC)	I _{D(DC)}	∓7.0	Α
Drain Current (pulse) *1	I _{D(pulse)}	∓28	Α
Total Power Dissipation (5 s) *2	P _T	2.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Notes: *1. PW≤10 μs, Duty Cycle≤1%

*2. Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt

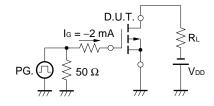
Electrical Characteristics (T_A = 25°C)

Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions	
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μA	V _{DS} = -12 V, V _{GS} = 0 V	
Gate Leakage Current	I _{GSS}			∓10	μA	$V_{GS} = \mp 8 \text{ V}, V_{DS} = 0 \text{ V}$	
Gate Cut-off Voltage	V _{GS(off)}	-0.4		-1.1	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	
Forward Transfer Admittance *1	y _{fs}	8.5			S	$V_{DS} = -5 \text{ V}, I_{D} = -3.5 \text{ A}$	
Drain to Source On-state Resistance *1	R _{DS(on)1}		20.5	28	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -3.5 \text{ A}$	
	R _{DS(on)2}		25.7	35	mΩ	$V_{GS} = -2.5 \text{ V}, I_D = -3.5 \text{ A}$	
	R _{DS(on)3}		34.9	59	mΩ	$V_{GS} = -1.8 \text{ V}, I_D = -3.5 \text{ A}$	
Input Capacitance	C _{iss}		1260		pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$	
Output Capacitance	Coss		240		pF	f = 1.0 MHz	
Reverse Transfer Capacitance	C _{rss}		188		pF		
Turn-on Delay Time	t _{d (on)}		9.2		ns	$I_D = -3.5 \text{ A}, V_{DD} = -6.0 \text{ V},$	
Rise Time	t _r		3.9		ns	$V_{GS} = -4.0 \text{ V}, R_G = 6 \Omega$	
Turn-off Delay Time	t _{d (off)}		76		ns		
Fall Time	t _f		49		ns		
Total Gate Charge	Q_G		11.3		nC	$I_D = -7.0 \text{ A}$, $V_{DD} = -9.6 \text{ V}$,	
Gate to Source Charge	Q _{GS}		1.7		nC	$V_{GS} = -4.5 \text{ V}$	
Gate to Drain Charge	Q_{GD}		2.8		nC		
Body Diode Forward Voltage *1	V _{F(S-D)}			1.5	V	I _F = 7.0 A, V _{GS} = 0 V	

Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME

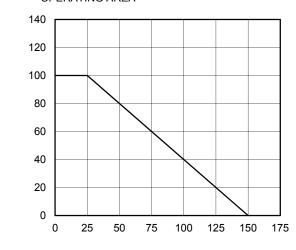
TEST CIRCUIT 2 GATE CHARGE



dT - Percentage of Rated Power - %

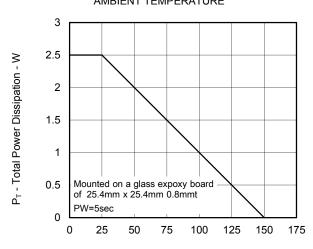
Typical Characteristics ($T_A = 25^{\circ}C$)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



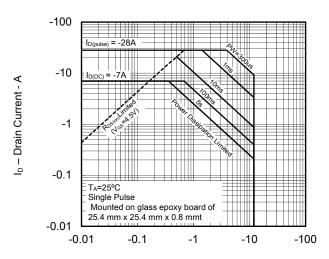
 T_A -Ambient Temperature - $^{\circ}C$

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



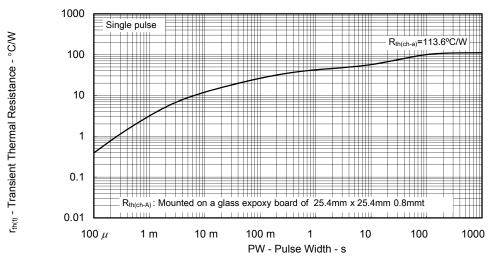
T_A -Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA



 $V_{\text{\scriptsize DS}}$ - Drain to Source Voltage - V

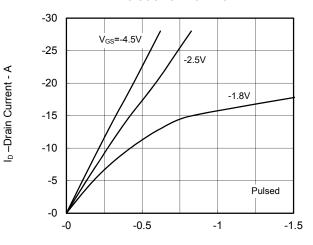
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



V_{GS(off)} – Gate to Source Cut-off Voltage - V

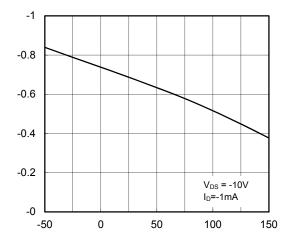
R_{DS(on)} - Drain to Source On-state Resistance - mΩ

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



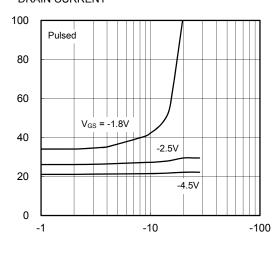
V_{DS} - Drain to Source Voltage - V

GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



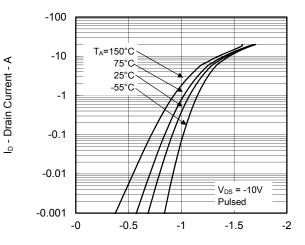
 T_{ch} - Channel Temperature - $^{\circ}C$

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



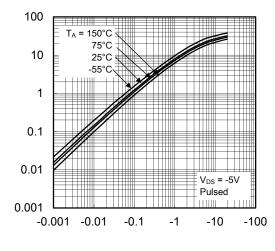
I_D - Drain Current - A

FORWARD TRANSFER CHARACTERISTICS



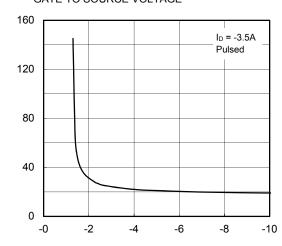
V_{GS} - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



I_D - Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



V_{GS} - Gate to Source Voltage - V

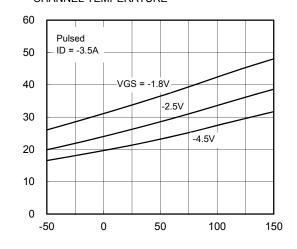
| y_{fs} | - Forward Transfer Admittance - S

 $R_{DS(on)}$ – Drain to Source On-state Resistance - $m\Omega$

 $R_{\text{DS(on)}}$ –Drain to Source On-state Resistance - $m\Omega$

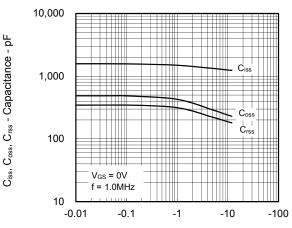
t_{d(on)}, t_f, t_{d(off)}, t_r - Switching Time -ns

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



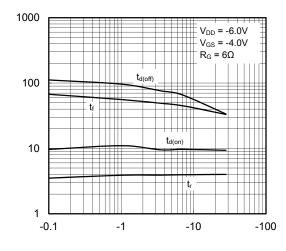
T_{ch} - Channel Temperature - °C

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



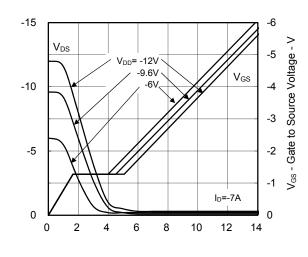
V_{DS} - Drain to Source Voltage - V

SWITCHING CHARACTERISTICS



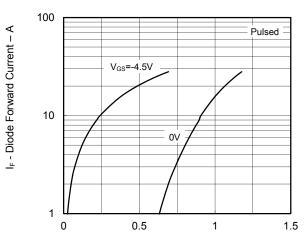
I_D - Drain Current - A

DYNAMIC INPUT/OUTPUT CHARACTERISTICS



 $\ensuremath{\mathsf{Q}}_{\ensuremath{\mathsf{G}}}$ - Gate Charge - nC

SOURCE TO DRAIN DIODE FORWARD VOLTAGE

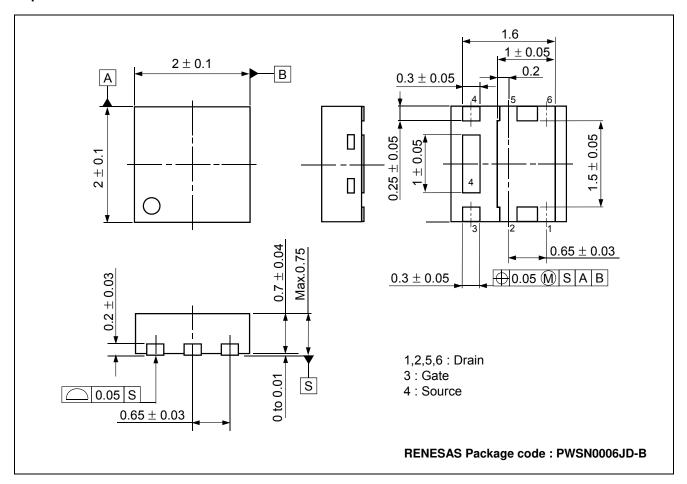


 $V_{F(S\!-\!D)}$ - Drain to Source Voltage - V

V_{DS} - Drain to Source Voltage - V

Package Drawings (Unit: mm)

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Equivalent Circuit



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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